

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) An electro-optical device, comprising:
 - a substrate;
 - a plurality of scanning lines formed above the substrate;
 - a plurality of data lines formed above the substrate and intersecting the plurality of scanning lines;
 - a plurality of thin-film transistors, each thin-film transistor being disposed in correspondence with a respective one of intersections of the plurality of data lines and the plurality of scanning lines;
 - a pixel electrode disposed with a corresponding thin-film transistor;
 - a storage capacitor comprising a portion of a semiconductor layer of the thin-film transistor as a first storage capacitor electrode and a second storage capacitor electrode comprising a conductive film of a gate electrode of the thin-film transistor;
 - a light shielding first conductive layer electrically connected between the semiconductor layer and the pixel electrode; and
 - a second conductive layer comprising a film of the first conductive layer as a storage capacitor line, at least partially overlapping the data lines in a plan view, and electrically connected to the second storage capacitor electrode.

2. (Previously Presented) The electro-optical device according to claim 1, the second conductive layer at least partially overlapping the pixel electrode in a plan view.

3. (Previously Presented) The electro-optical device according to claim 1, the first conductive layer being electrically connected to the semiconductor layer through a first contact hole and is electrically connected to the pixel electrode through a second contact hole.

4. (Previously Presented) The electro-optical device according to claim 1, the data lines being electrically connected to the semiconductor layer through a third contact hole.

5. (Previously Presented) The electro-optical device according to claim 1, the data lines not at least partially overlapping the pixel electrode in a plan view.

6. (Previously Presented) The electro-optical device according to claim 1, the second conductive layer being electrically connected to a constant-potential line.

7. (Previously Presented) The electro-optical device according to claim 1, further comprising a light-shielding film formed on the substrate side of at least a channel region of the semiconductor layer with an underlying insulating film therebetween.

8. (Previously Presented) The electro-optical device according to claim 1, the first conductive layer and the second conductive layer comprising a high-melting point metal.

9. (Previously Presented) The electro-optical device according to claim 1, the second conductive layer and the data lines being at least partially disposed opposite to each other with an interlayer insulating film therebetween.

10.-13. (Canceled)

14. (Previously Presented) The electro-optical device according to claim 3, the second conductive layer being electrically connected to the second storage capacitor electrode through a fourth contact hole, and the fourth contact hole being opened when opening the first contact hole.

15.-20. (Canceled)

21. (Previously Presented) The electro-optical device according to claim 1, the second conductive layer being shaped like an island in a plan view and at least partially delimiting a region along the data lines in a pixel-aperture region.

22. (Canceled)

23. (Previously Presented) The electro-optical device according to claim 1, the second conductive layer being formed like a grid excluding a region in which the first conductive layer is present in a plan view and delimiting regions along the data lines and the scanning lines in the pixel-aperture region.

24. (Previously Presented) The electro-optical device according to claim 1, the semiconductor layer and the first conductive layer being connected to each other with an interconnecting conductive layer comprising a film comprising the data lines therebetween.

25.-27. (Canceled)

28. (Previously Presented) A method for fabricating an electro-optical device comprising a substrate, a plurality of scanning lines, a plurality of data lines, a thin-film transistor including a gate electrode and disposed in correspondence with intersections of the plurality of data lines and the plurality of scanning lines, and a pixel electrode disposed in correspondence with the thin-film transistor, the method comprising the steps of:

forming a semiconductor layer for producing a source region, a channel region, and a drain region on the substrate;

forming an insulating thin film on the semiconductor layer;

forming the gate electrode and one electrode of a storage capacitor on the insulating thin film;

forming a first interlayer insulating film on the gate electrode and the one electrode of the storage capacitor;

making a first contact hole leading to the semiconductor layer in the first interlayer insulating film;

forming the data lines on the first interlayer insulating film and simultaneously forming an interconnecting conductive layer comprising a film comprising the data lines so as to be electrically connected to the semiconductor layer through the first contact hole;

forming a second interlayer insulating film on the data lines and the interconnecting conductive layer;

making a second contact hole leading to the interconnecting conductive layer in the second interlayer insulating film;

making a third contact hole leading to the electrode of the storage capacitor in the second interlayer insulating film;

forming a light-shielding first conductive film on the second interlayer insulating film so as to be electrically connected to the interconnecting conductive layer through the second contact hole, and simultaneously forming a second conductive layer comprising a film of conductive layer disposed on the second interlayer insulating film as a storage capacitor line so as to be electrically connected to the one electrode of a storage capacitor through the third contact hole and overlap the data lines in a plan view;

forming a third interlayer insulating film on the first conductive layer and the second conductive layer;

making a fourth contact hole leading to the first conductive layer in the third interlayer insulating film; and

forming the pixel electrode so as to be electrically connected to the first conductive layer through the fourth contact hole.

29. (Previously Presented) The method for fabricating an electro-optical device according to claim 28, further comprising the step of:

making a fifth contact hole leading to the semiconductor layer in the first interlayer insulating film after the step of forming the first interlayer insulating film, in the step of forming the data lines, the data lines being formed so as to be electrically connected to the semiconductor layer through the fifth contact hole.

30. (Previously Presented) An electronic apparatus comprising the electro-optical device according to claim 1.

31. (Previously Presented) The electro-optical device according to claim 1, the first conductive layer and the second conductive layer being formed with a same film.

32. (Previously Presented) The electro-optical device according to claim 1, the second storage capacitor electrode being shaped like an island as viewed in plan.

33. (Previously Presented) The electro-optical device according to claim 1, the second conductive layer being disposed at least partially above the data lines.

34. (Currently Amended) An electro-optical device comprising:

- a substrate;
- a plurality of scanning lines formed above the substrate;
- a plurality of data lines formed above the substrate and intersecting the plurality of scanning lines;
- a plurality of thin-film transistors, each thin-film transistor being disposed in correspondence with a respective one of intersections of the plurality of data lines and the plurality of scanning lines, each transistor including a semiconductor layer;
- a storage capacitor including:
 - a first storage capacitor electrode formed from a portion of the semiconductor layer of a corresponding thin-film transistor,
 - a second storage capacitor electrode, and
 - an insulating thin film interposed between the first storage capacitor electrode and the second storage capacitor electrode; and
- a light-shielding conductive layer, as a storage capacitor line, electrically connected to the second storage capacitor electrode.

35. (Previously Presented) The electro-optical device according to claim 34, the light-shielding conductive layer at least partially overlapping the data lines as viewed in plan.

36. (Previously Presented) The electro-optical device according to claim 34, the storage capacitor electrode being shaped like an island as viewed in plan.

37. (Previously Presented) The electro-optical device according to claim 34, the light-shielding conductive layer being disposed at least partially above the data lines.

38. (Previously Presented) The electro-optical device according to claim 34, the light-shielding conductive layer being formed like a grid.

39. (Previously Presented) The electro-optical device according to claim 34, the light-shielding conductor layer being formed in a grid shape excluding a region, and further comprising:

a pixel electrode disposed with a corresponding thin-film transistor; and
style="padding-left: 40px;">a second conductor layer electrically connected to the semiconductor layer and the pixel electrode through the region.

40. (Previously Presented) A method for fabricating an electro-optical device comprising a substrate, a plurality of scanning lines, a plurality of data lines, and a thin-film transistor disposed in correspondence with intersections of the plurality of data lines and the plurality of scanning lines, the method comprising:

forming a semiconductor layer for producing a source region, a channel region, a drain region, and a first storage capacitor electrode on the substrate;

forming an insulating thin film on the semiconductor layer;

forming a second storage capacitor electrode on the insulating thin film in opposition to the first storage capacitor electrode;

forming an interlayer insulating film above the second storage capacitor electrode;

making a contact hole leading to the second storage capacitor electrode in the interlayer insulating film; and

forming a light-shielding first conductive film on the interlayer insulating film and into the contact hole as a storage capacitor line electrically connected to the second storage capacitor electrode through the contact hole.